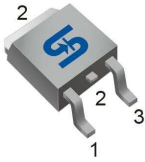


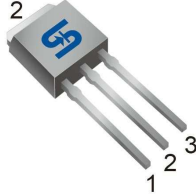
TSM70N10

100V N-Channel Power MOSFET

TO-252
(DPAK)



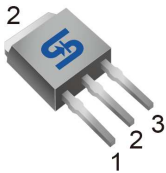
TO-251
(IPAK)



Pin Definition:

1. Gate
2. Drain
3. Source

TO-251S
(IPAK SL)



Key Parameter Performance

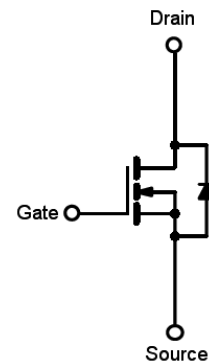
Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on)}(max)$	13	mΩ
Q_g	145	nC

Ordering Information

Part No.	Package	Packing
TSM70N10CP ROG	TO-252	2.5kpcs / 13" Reel
TSM70N10CH C5G	TO-251	75pcs / Tube
TSM70N10CH X0G	TO-251S	75pcs / Tube

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^(Note 3)	$T_C=25^\circ\text{C}$	70	A
	$T_C=70^\circ\text{C}$	61	
	$T_A=25^\circ\text{C}$	12	
	$T_A=70^\circ\text{C}$	9	
Drain Current-Pulsed ^(Note 1)	I_{DM}	150	A
Avalanche Current, $L=0.5\text{mH}$	I_{AS}, I_{AR}	25	A
Avalanche Energy, $L=0.5\text{mH}$	E_{AS}, E_{AR}	156	mJ
Maximum Power Dissipation ^(Note 2)	$T_C=25^\circ\text{C}$	120	W
	$T_C=70^\circ\text{C}$	80	
	$T_A=25^\circ\text{C}$	8.3	
	$T_A=70^\circ\text{C}$	5.3	
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	1	$^{\circ}\text{C/W}$
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$

Electrical Specifications ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

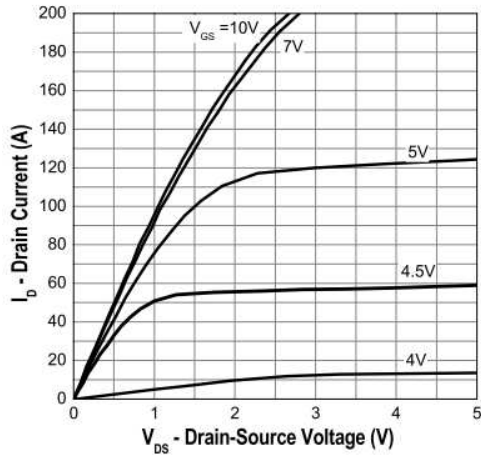
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	100	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	$R_{DS(ON)}$	--	10	13	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 50V, I_D = 30A,$ $V_{GS} = 10V$	Q_g	--	145	--	nC
Gate-Source Charge		Q_{gs}	--	25	--	
Gate-Drain Charge		Q_{gd}	--	43	--	
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	4300	--	pF
Output Capacitance		C_{oss}	--	300	--	
Reverse Transfer Capacitance		C_{rss}	--	120	--	
Switching						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 50V,$ $R_G = 3\Omega$	$t_{d(on)}$	--	27	--	ns
Turn-On Rise Time		t_r	--	13	--	
Turn-Off Delay Time		$t_{d(off)}$	--	15	--	
Turn-Off Fall Time		t_f	--	42	--	
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	V_{SD}	--	0.8	1.3	V
Reverse Recovery Time	$I_S = 30A, T_J=25^{\circ}C$	t_{rr}	--	165	--	ns
Reverse Recovery Charge	$di/dt = 100A/\mu s$	Q_{rr}	--	175	--	nC

Notes:

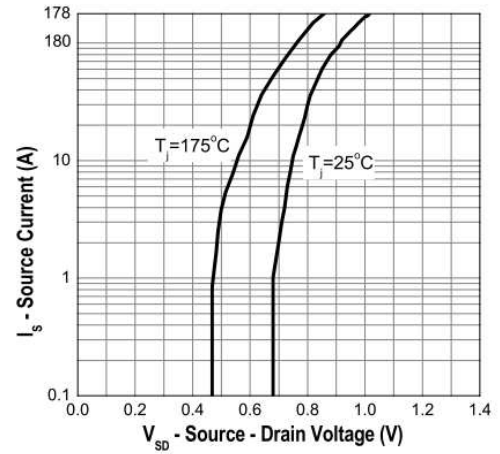
- Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.
- The maximum current is limited by package.

Electrical Characteristics Curves

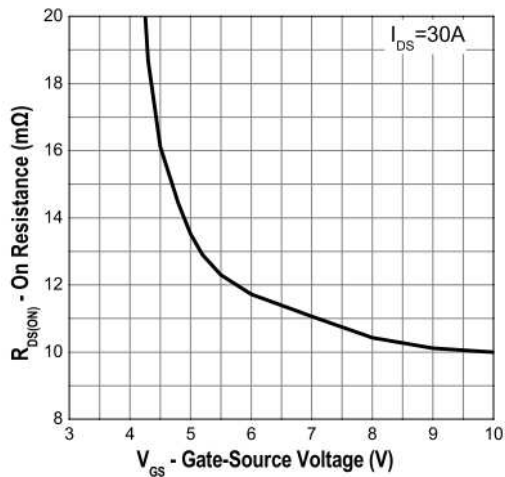
Output Characteristics



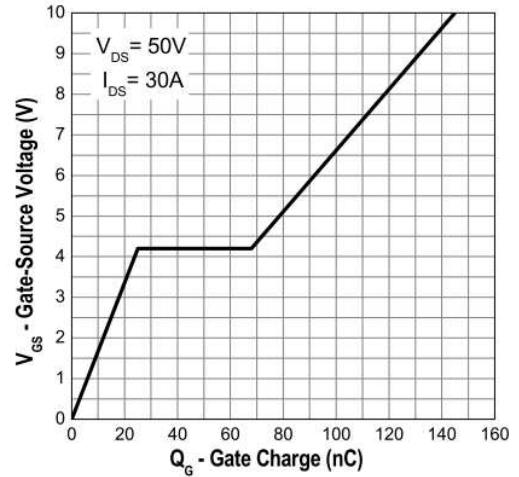
Transfer Characteristics



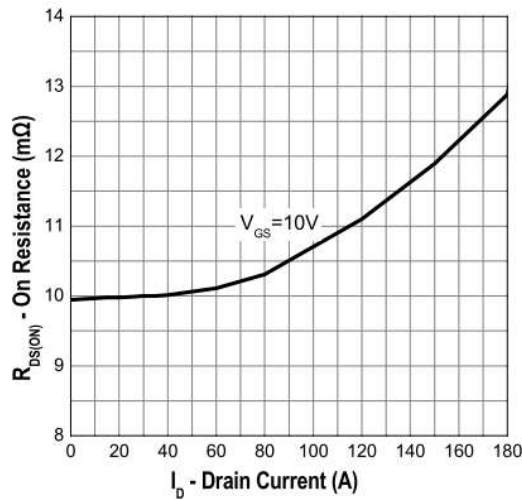
On-Resistance vs. Gate-Source Voltage



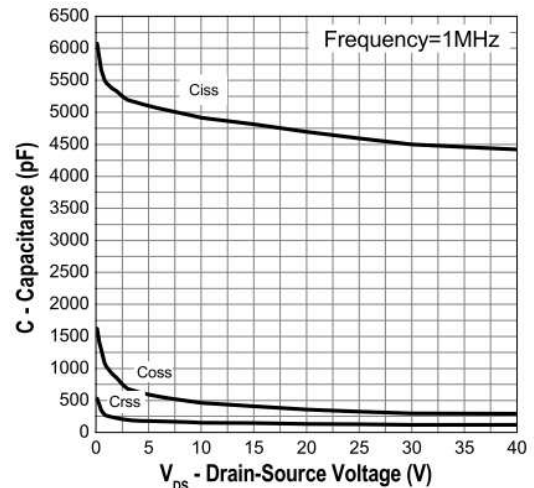
Gate Charge



On-Resistance vs. Junction Temperature

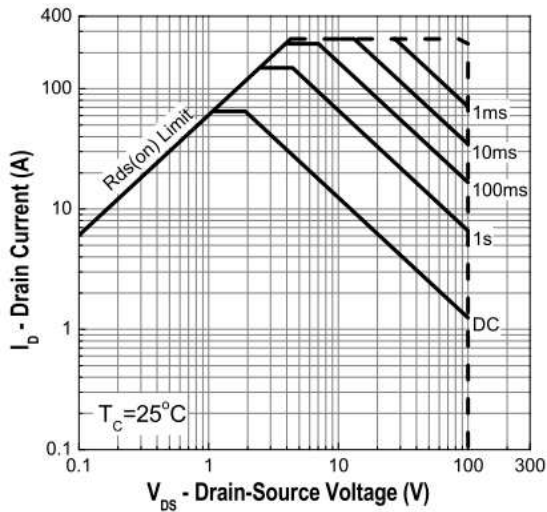


Capacitance

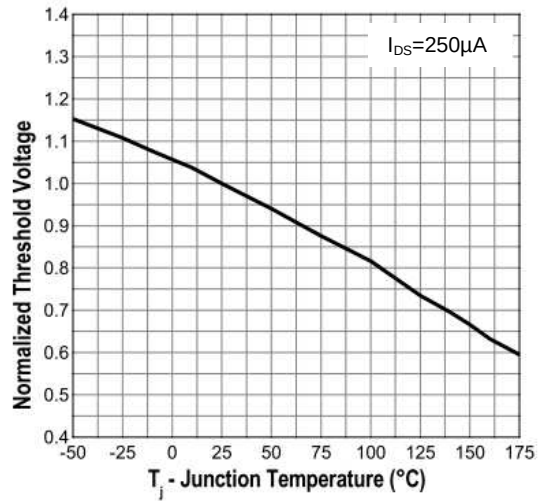


Electrical Characteristics Curves

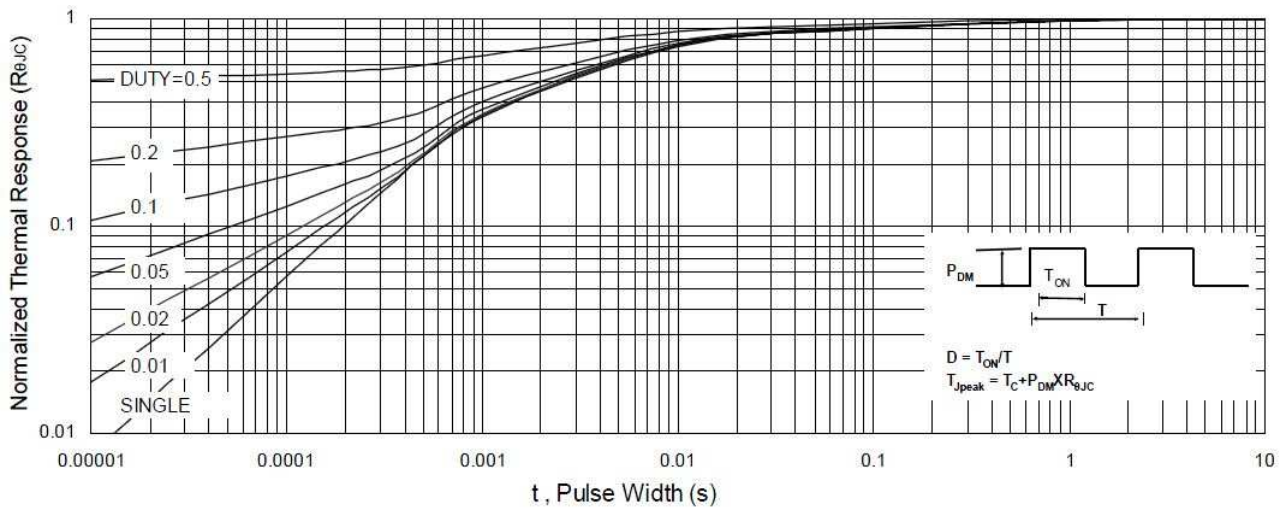
Maximum Safe Operating Area



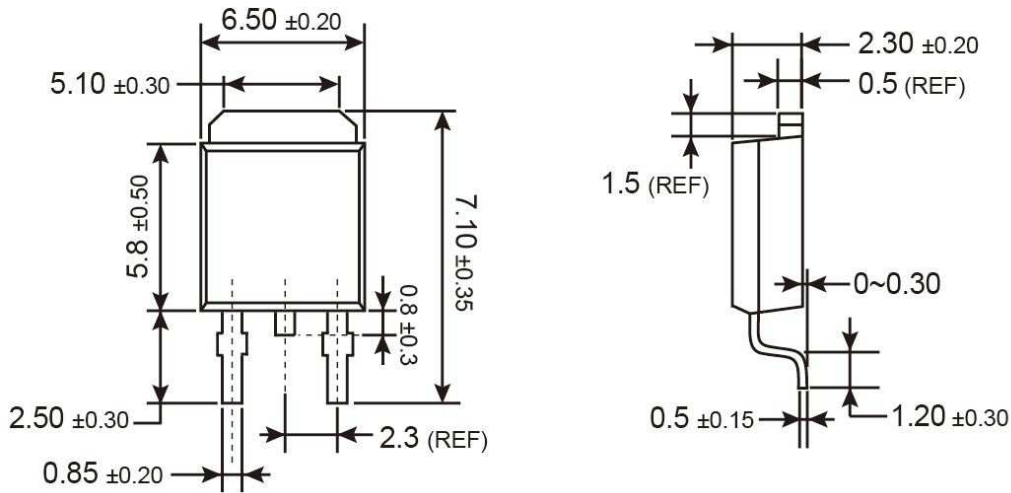
Threshold Voltage vs. Temperature



Normalized Thermal Transient Impedance, Junction-to-Ambient

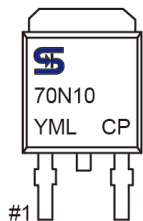


TO-252 Mechanical Drawing



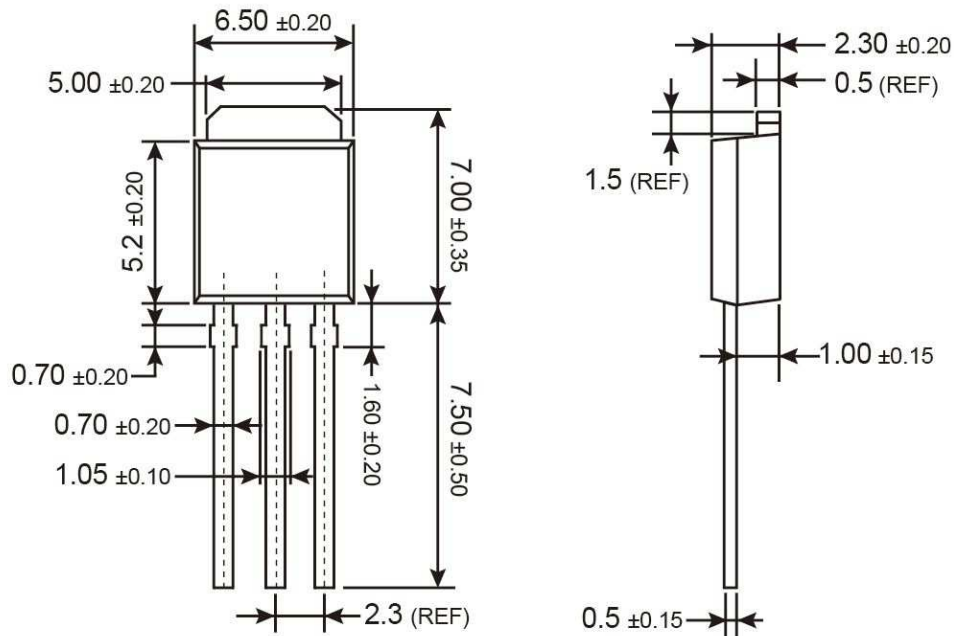
Unit: Millimeters

Marking Diagram



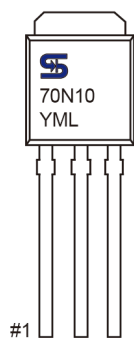
- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

TO-251 (IPAK) Mechanical Drawing



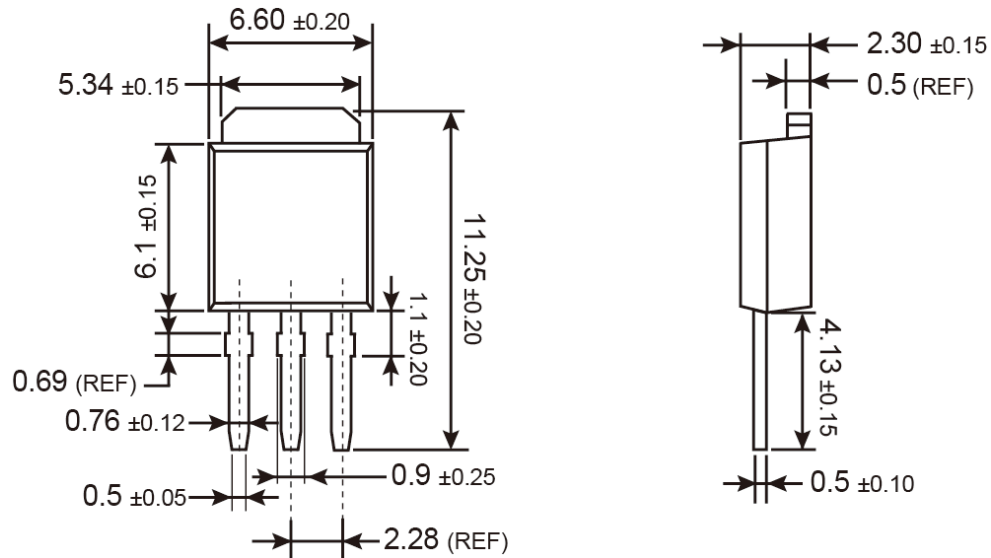
Unit: Millimeters

Marking Diagram



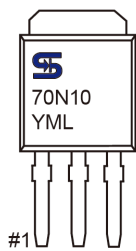
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- L** = Lot Code

TO-251S (IPAK SL) Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

TSM70N10

100V N-Channel Power MOSFET

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